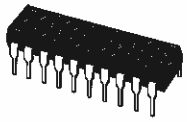
SGS-THOMSON MICROELECTRONICS

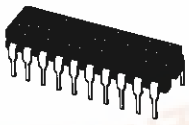
M54HC540/541
M74HC540/541

OCTAL BUS BUFFER WITH 3 STATE OUTPUTS
HC540: INVERTED - HC541 NON INVERTED

- HIGH SPEED
  t_{PD} = 10 ns (TYP.) at V_{CC} = 5V
- LOW POWER DISSIPATION
  I_{CC} = 4 µA (MAX.) at T_A = 25 °C
- HIGH NOISE IMMUNITY
  $V_{NIH} = V_{INL}$ = 28 % V_{CC} (MIN.)
- OUTPUT DRIVE CAPABILITY
  15 LSTTL LOADS
- SYMMETRICAL OUTPUT IMPEDANCE
  $|I_{OH}| = I_{OL}$ = 6 mA (MIN)
- BALANCED PROPAGATION DELAYS
  $t_{PLH} = t_{PHL}$
- WIDE OPERATING VOLTAGE RANGE
  V_{CC} (OPR) = 2V to 6V
- PIN AND FUNCTION COMPATIBLE
  WITH 54/74LS540/541



B1R
(Plastic Package)



F1R
(Ceramic Package)

M1R
(Micro Package)

C1R
(Chip Carrier)

ORDER CODES :

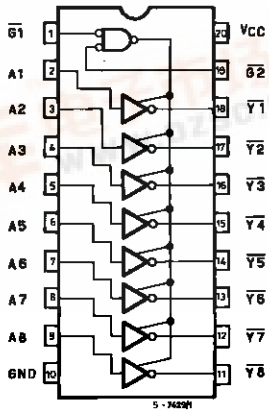
M54HCXXXF1R	M74HCXXXM1R
M74HCXXXB1R	M74HCXXXC1R

DESCRIPTION

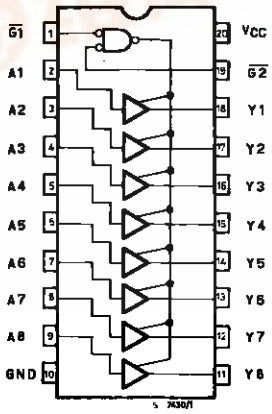
The M54/74HC540 and HC541 are high speed CMOS OCTAL BUS BUFFERS (3-STATE) fabricated in silicon gate C^2MOS technology. They have the same high speed performance of LSTTL combined with true CMOS low power consumption. The HC540 is an inverting buffer and HC541 is a non inverting buffer.
The 3 STATE control gate operates as a two input AND such that if either $\overline{G1}$ and $\overline{G2}$ are high, all eight output are in the high impedance state. In order to enhance PC board layout, the HC540 and HC541 offers a pinout having inputs and outputs on opposite sides of the package.
All inputs are equipped with protection circuits against static discharge and transient excess voltage.

PIN CONNECTION (top view)

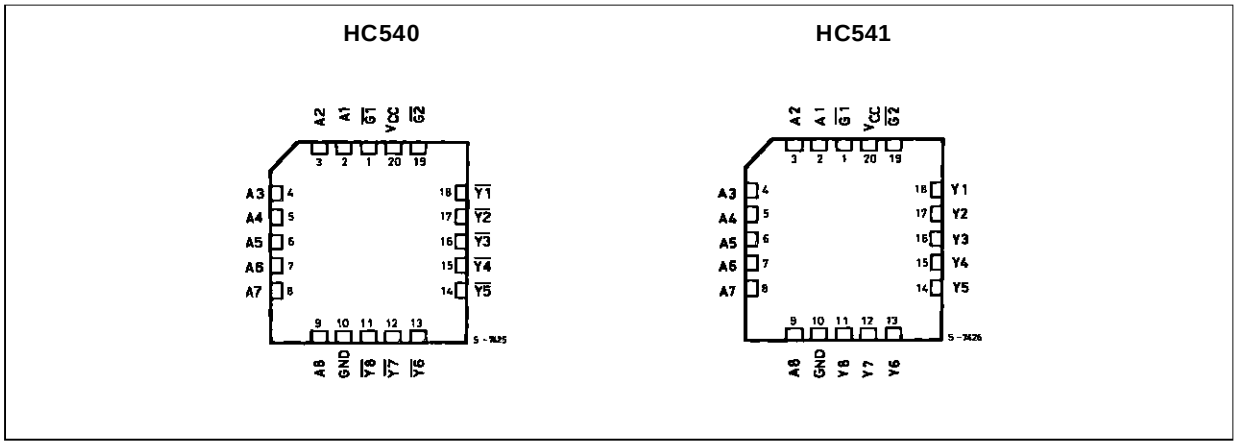
HC540



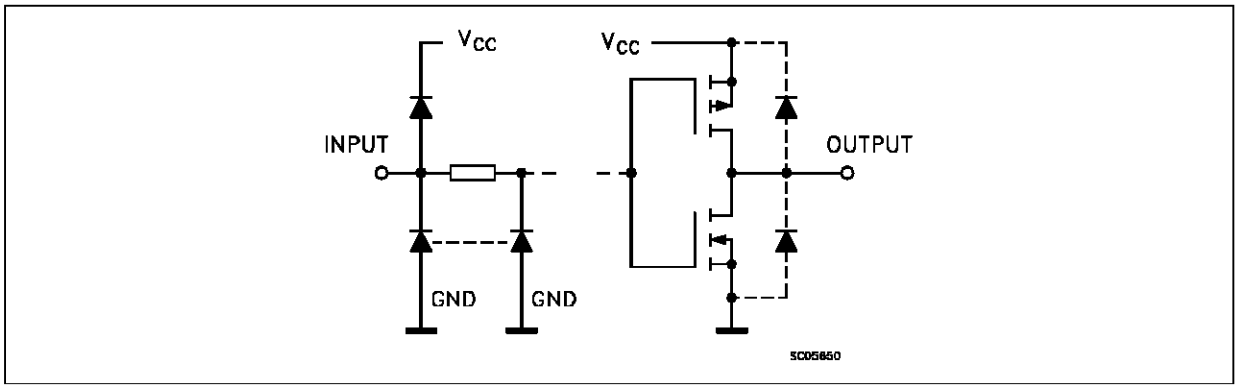
HC541



CHIP CARRIER



INPUT AND OUTPUT EQUIVALENT CIRCUIT



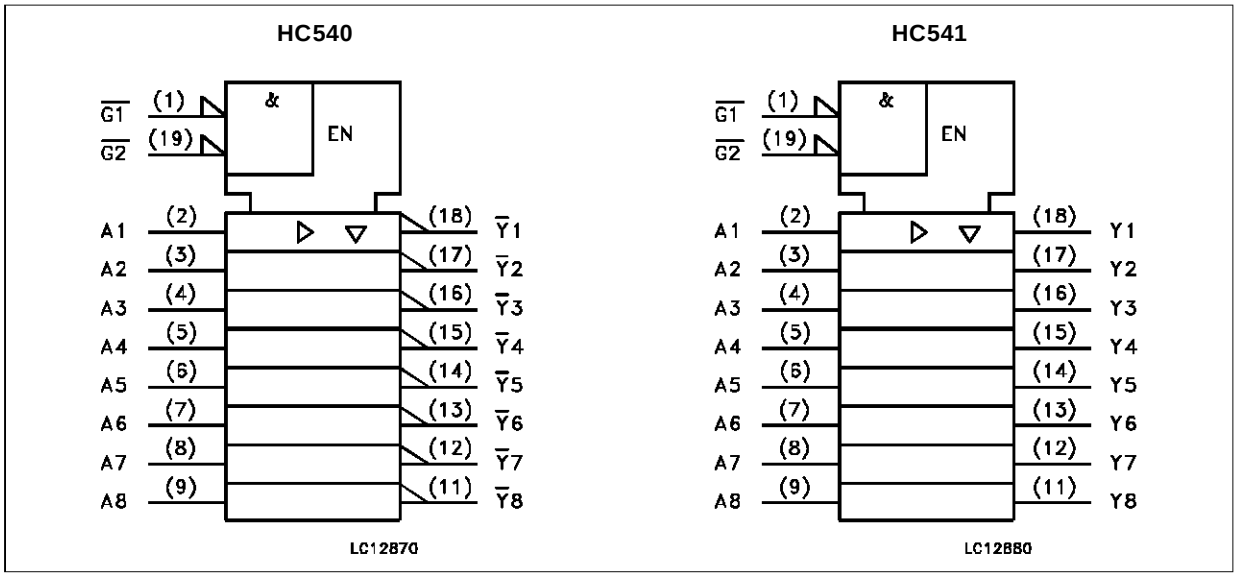
PIN DESCRIPTION (HC540)

PIN No	SYMBOL	NAME AND FUNCTION
1, 19	$\overline{1G}$, $\overline{G2}$	Output Enable Inputs
2, 3, 4, 5, 6, 7, 8, 9	A1 to A8	Data Inputs
18, 17, 16, 15, 14, 13, 12, 11	$\overline{Y1}$ to $\overline{Y8}$	Bus Outputs
10	GND	Ground (0V)
20	V_{CC}	Positive Supply Voltage

PIN DESCRIPTION (HC541)

PIN No	SYMBOL	NAME AND FUNCTION
1, 19	$\overline{1G}$, $\overline{G2}$	Output Enable Inputs
2, 3, 4, 5, 6, 7, 8, 9	A1 to A8	Data Inputs
18, 17, 16, 15, 14, 13, 12, 11	Y1 to Y8	Bus Outputs
10	GND	Ground (0V)
20	V_{CC}	Positive Supply Voltage

IEC LOGIC SYMBOLS

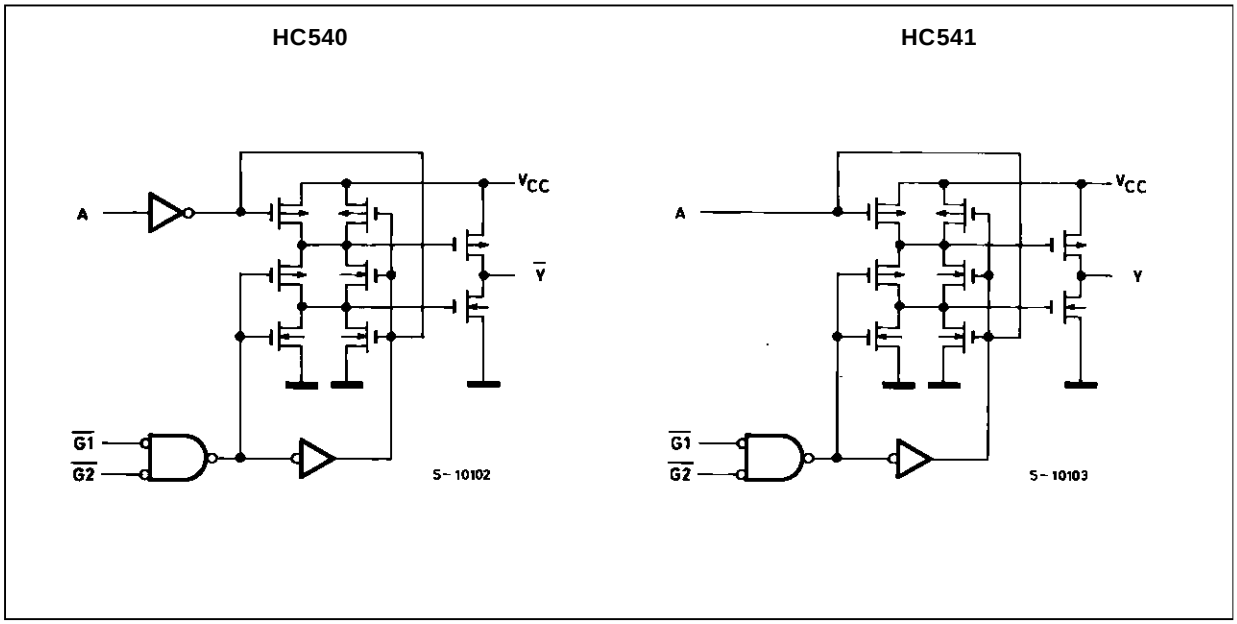


TRUTH TABLE

INPUT			OUTPUT	
$\overline{G1}$	$\overline{G2}$	An	$\overline{Yn}$ (HC540)	Yn (HC541)
H	X	X	Z	Z
X	H	X	Z	Z
L	L	H	L	H
L	L	L	H	L

X: "H" or "L"
Z: High impedance

CIRCUIT SCHEMATIC (Per Circuit)



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CC}	Supply Voltage	-0.5 to +7	V
V_I	DC Input Voltage	-0.5 to V_{CC} + 0.5	V
V_O	DC Output Voltage	-0.5 to V_{CC} + 0.5	V
I_{IK}	DC Input Diode Current	± 20	mA
I_{OK}	DC Output Diode Current	± 20	mA
I_O	DC Output Source Sink Current Per Output Pin	± 35	mA
I_{CC} or I_{GND}	DC V_{CC} or Ground Current	± 70	mA
P_D	Power Dissipation	500 (*)	mW
T_{stg}	Storage Temperature	-65 to +150	°C
T_L	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied.
(*) 500 mW: ≅ 65 °C derate to 300 mW by 10mW/°C: 65 °C to 85 °C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Value	Unit
V_{CC}	Supply Voltage		2 to 6	V
V_I	Input Voltage		0 to V_{CC}	V
V_O	Output Voltage		0 to V_{CC}	V
T_{op}	Operating Temperature: **M54HC** Series **M74HC** Series		-55 to +125 -40 to +85	°C °C
t_r, t_f	Input Rise and Fall Time	V_{CC} = 2 V	0 to 1000	ns
		V_{CC} = 4.5 V	0 to 500	
		V_{CC} = 6 V	0 to 400	

DC SPECIFICATIONS

Symbol	Parameter	Test Conditions			Value							Unit
		V_{CC} (V)			T_A = 25 °C 54HC and 74HC			-40 to 85 °C 74HC		-55 to 125 °C 54HC		
					Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
V_{IH}	High Level Input Voltage	2.0			1.5			1.5		1.5		V
		4.5			3.15			3.15		3.15		
		6.0			4.2			4.2		4.2		
V_{IL}	Low Level Input Voltage	2.0					0.5		0.5		0.5	V
		4.5					1.35		1.35		1.35	
		6.0					1.8		1.8		1.8	
V_{OH}	High Level Output Voltage	2.0	V_I = V_{IH} or V_{IL}	I_O=-20 µA	1.9	2.0		1.9		1.9		V
		4.5			4.4	4.5		4.4		4.4		
		6.0			5.9	6.0		5.9		5.9		
		4.5		I_O=-6.0 mA	4.18	4.31		4.13		4.10		
		6.0		I_O=-7.8 mA	5.68	5.8		5.63		5.60		
V_{OL}	Low Level Output Voltage	2.0	V_I = V_{IH} or V_{IL}	I_O= 20 µA		0.0	0.1		0.1		0.1	V
		4.5				0.0	0.1		0.1		0.1	
		6.0				0.0	0.1		0.1		0.1	
		4.5		I_O= 6.0 mA		0.17	0.26		0.33		0.40	
		6.0		I_O= 7.8 mA		0.18	0.26		0.33		0.40	
I_I	Input Leakage Current	6.0	V_I = V_{CC} or GND				±0.1		±1		±1	µA
I_{OZ}	3 State Output Off State Current	6.0	V_I = V_{IH} or V_{IL} V_O = V_{CC} or GND				±0.5		±5		±10	µA
I_{CC}	Quiescent Supply Current	6.0	V_I = V_{CC} or GND				4		40		80	µA

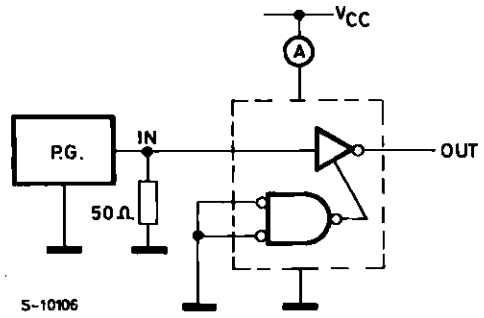
AC ELECTRICAL CHARACTERISTICS (C_L = 50 pF, Input $t_r = t_f$ = 6 ns)

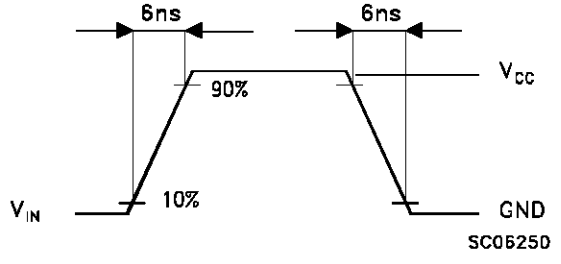
Symbol	Parameter	Test Conditions			Value							Unit
		V_{CC} (V)	C_L (pF)		T_A = 25 °C 54HC and 74HC			-40 to 85 °C 74HC		-55 to 125 °C 54HC		
					Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
t_{TLH} t_{THL}	Output Transition Time	2.0	50			25	60		75		90	ns
		4.5				7	12		19		18	
		6.0				6	10		13		15	
t_{PLH} t_{PHL}	Propagation Delay Time	2.0	50			40	85		105		130	ns
		4.5				10	17		21		26	
		6.0				9	14		18		22	
		2.0	150			56	115		145		175	ns
		4.5				14	23		29		35	
		6.0				12	20		25		30	
t_{PZL} t_{PZH}	Output Enable Time	2.0	50	R_L = 1KΩ		47	110		140		165	ns
		4.5				13	22		28		33	
		6.0				11	19		24		28	
		2.0	150	R_L = 1KΩ		61	135		170		205	ns
		4.5				17	27		34		41	
		6.0				14	23		29		35	
t_{PLZ} t_{PHZ}	Output Disable Time	2.0	50	R_L = 1KΩ		52	110		140		165	ns
		4.5				15	22		28		33	
		6.0				13	19		24		28	
C_{IN}	Input Capacitance					5	10		10		10	pF
C_{PD} (*)	Power Dissipation Capacitance					31						pF

(*) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operting current can be obtained by the following equation. $I_{CC}(opr) = C_{PD} \bullet V_{CC} \bullet f_{IN} + I_{CC}/8$ (per gate)

TEST CIRCUIT I_{CC} (Opr.)

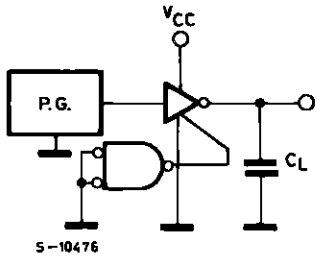
HC540



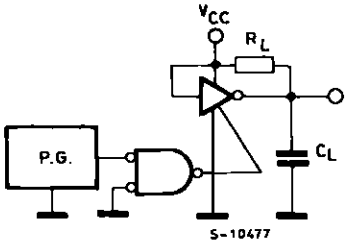


SWITCHING CHARACTERISTICS TEST CIRCUIT

HC540



S-10476



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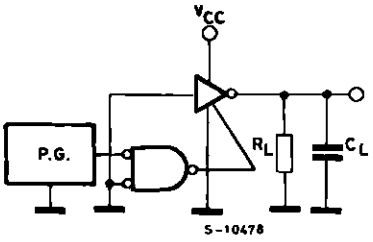

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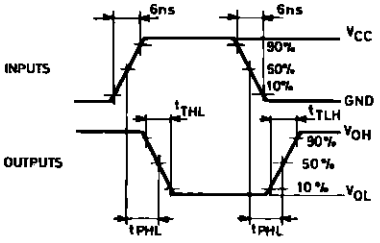

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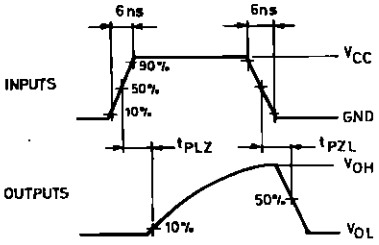

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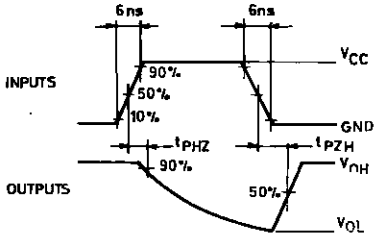
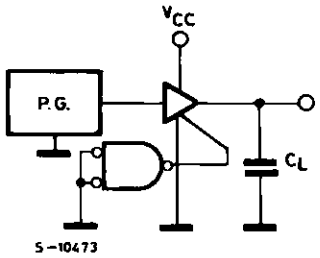


S-10472

HC541



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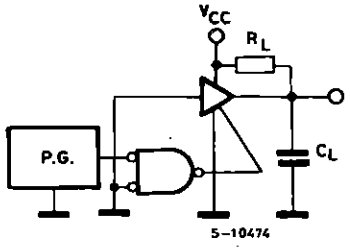

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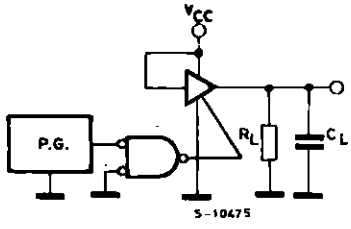

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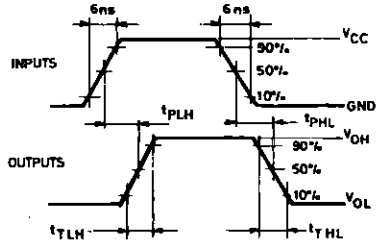

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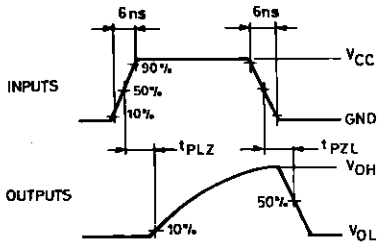

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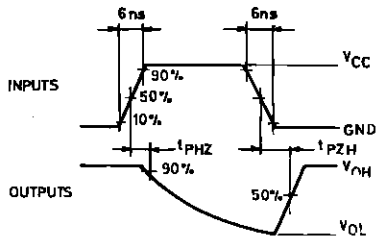
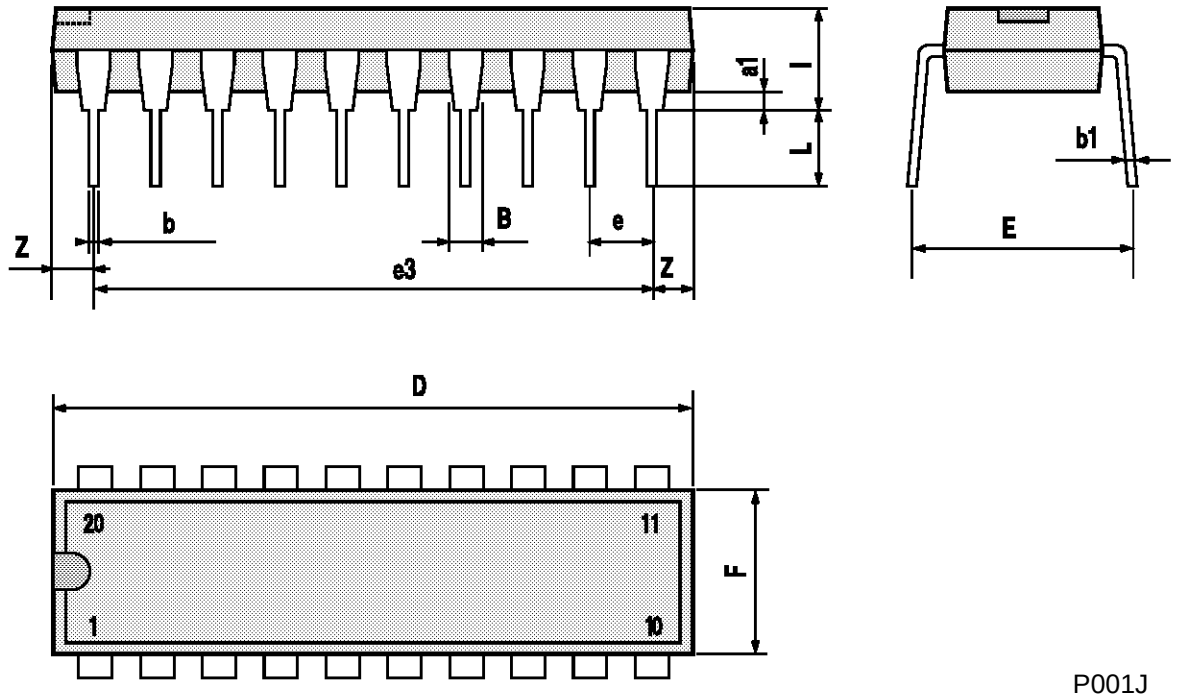


S-10472

Plastic DIP20 (0.25) MECHANICAL DATA

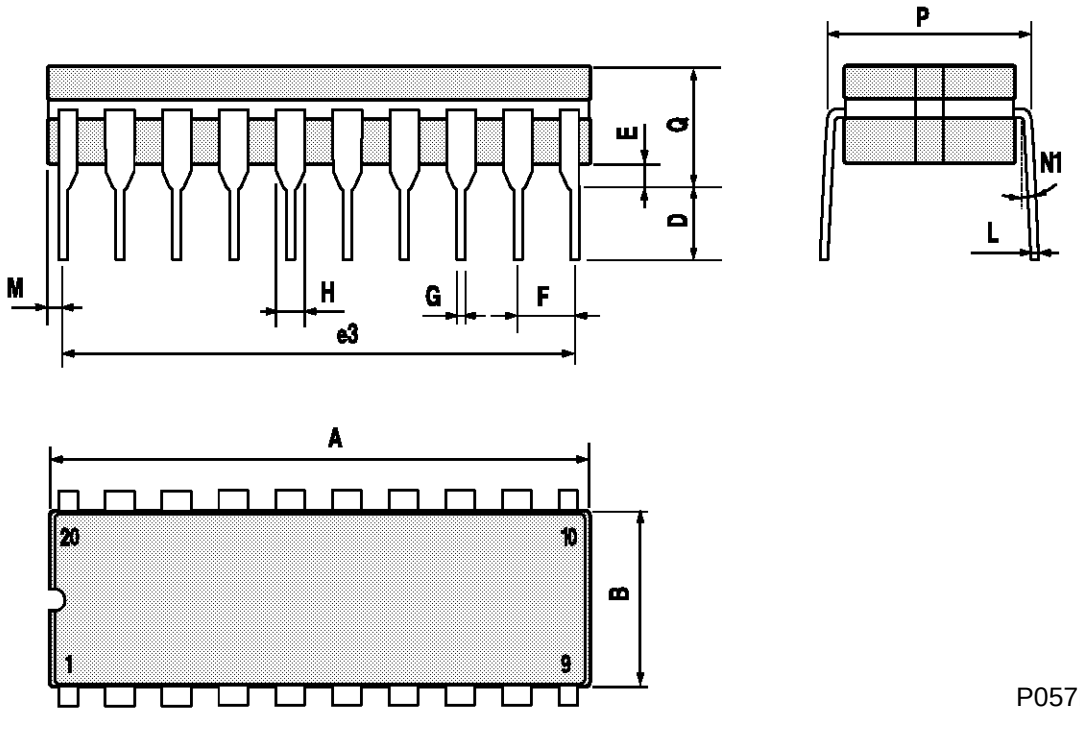
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
a1	0.254			0.010		
B	1.39		1.65	0.055		0.065
b		0.45			0.018	
b1		0.25			0.010	
D			25.4			1.000
E		8.5			0.335	
e		2.54			0.100	
e3		22.86			0.900	
F			7.1			0.280
I			3.93			0.155
L		3.3			0.130	
Z			1.34			0.053



P001J

Ceramic DIP20 MECHANICAL DATA

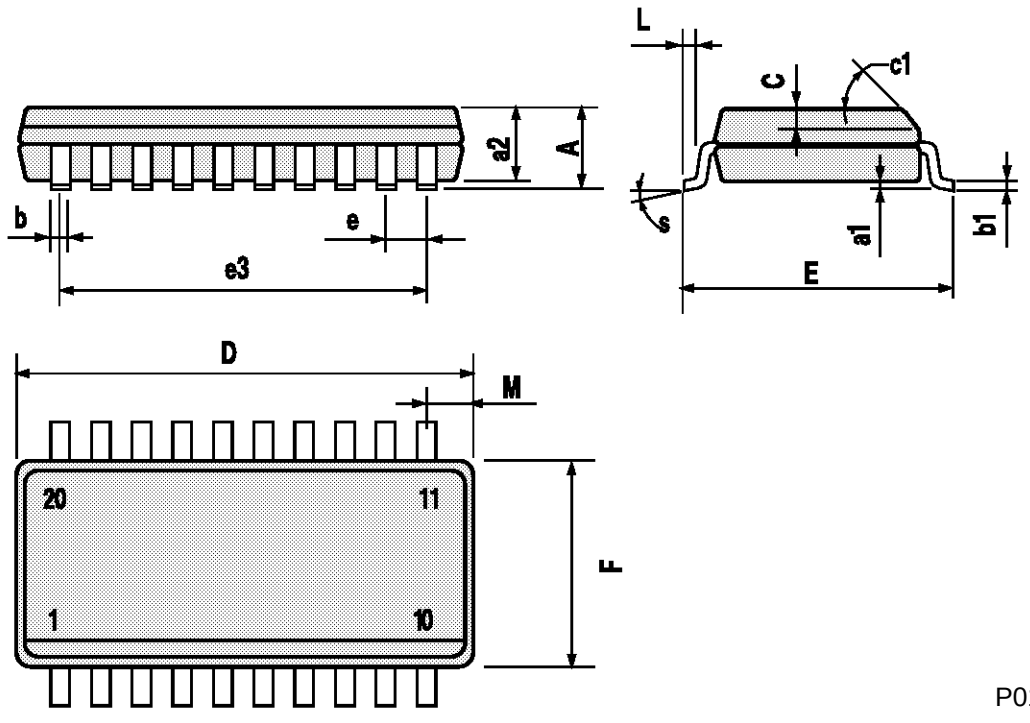
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			25			0.984
B			7.8			0.307
D		3.3			0.130	
E	0.5		1.78	0.020		0.070
e3		22.86			0.900	
F	2.29		2.79	0.090		0.110
G	0.4		0.55	0.016		0.022
I	1.27		1.52	0.050		0.060
L	0.22		0.31	0.009		0.012
M	0.51		1.27	0.020		0.050
N1	4° (min.), 15° (max.)					
P	7.9		8.13	0.311		0.320
Q			5.71			0.225



P057H

SO20 MECHANICAL DATA

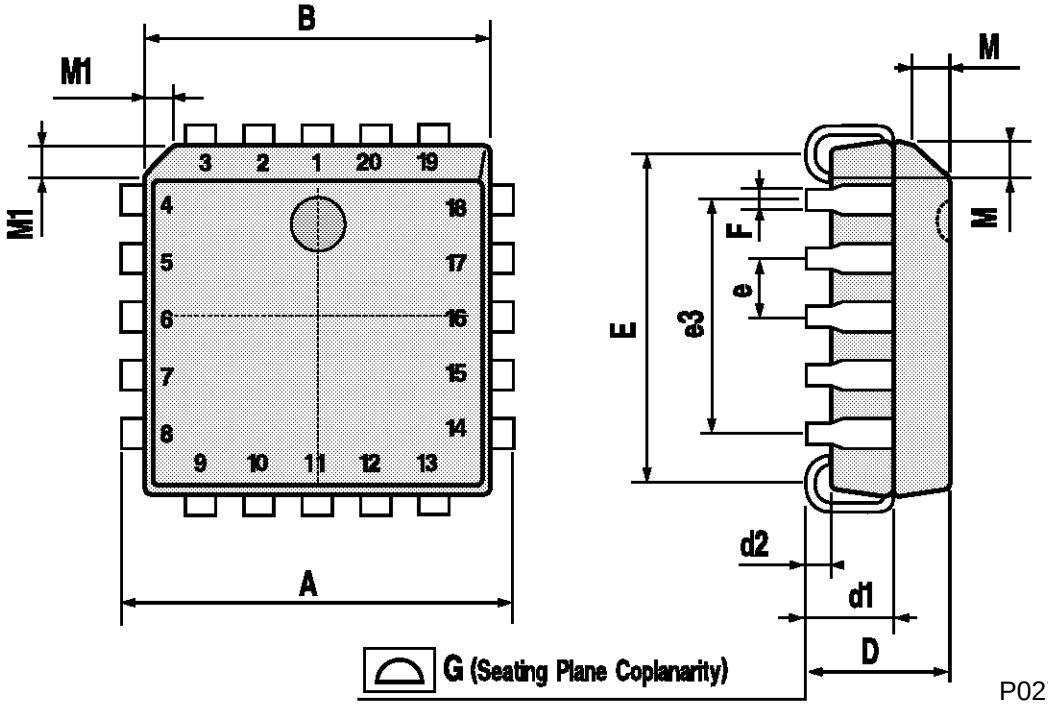
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			2.65			0.104
a1	0.10		0.20	0.004		0.007
a2			2.45			0.096
b	0.35		0.49	0.013		0.019
b1	0.23		0.32	0.009		0.012
C		0.50			0.020	
c1	45° (typ.)					
D	12.60		13.00	0.496		0.512
E	10.00		10.65	0.393		0.419
e		1.27			0.050	
e3		11.43			0.450	
F	7.40		7.60	0.291		0.299
L	0.50		1.27	0.19		0.050
M			0.75			0.029
S	8° (max.)					



P013L

PLCC20 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	9.78		10.03	0.385		0.395
B	8.89		9.04	0.350		0.356
D	4.2		4.57	0.165		0.180
d1		2.54			0.100	
d2		0.56			0.022	
E	7.37		8.38	0.290		0.330
e		1.27			0.050	
e3		5.08			0.200	
F		0.38			0.015	
G			0.101			0.004
M		1.27			0.050	
M1		1.14			0.045	



P027A